

DUAL N-Channel Enhancement Mode Power MOSFET

Description

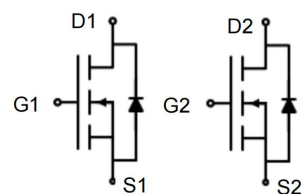
The G120N02D32 uses advanced trench technology to provide excellent $R_{DS(ON)}$, low gate charge. It can be used in a wide variety of applications.

General Features

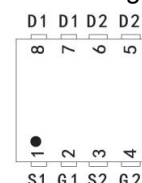
- V_{DS} 20V
- I_D (at $V_{GS} = 10V$) 26A
- $R_{DS(ON)}$ (at $V_{GS} = 4.5V$) < 11m Ω
- $R_{DS(ON)}$ (at $V_{GS} = 2.5V$) < 14m Ω
- 100% Avalanche Tested
- RoHS Compliant

Application

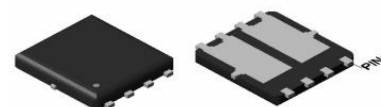
- Power switch
- DC/DC converters



Schematic diagram



pin assignment



DFN3X3-8L Dual

Ordering Information

Device	Package	Marking	Packaging
G120N02D32	DFN3X3-8L Dual	G120N02	5000pcs/Reel

Absolute Maximum Ratings $T_C = 25^\circ\text{C}$, unless otherwise noted

Parameter	Symbol	Value	Unit
Drain-Source Voltage	V_{DS}	20	V
Continuous Drain Current	I_D	26	A
		16	
Pulsed Drain Current (note1)	I_{DM}	104	A
Gate-Source Voltage	V_{GS}	± 12	V
Power Dissipation	P_D	15	W
Single pulse avalanche energy (note2)	E_{AS}	30	mJ
Operating Junction and Storage Temperature Range	T_J, T_{stg}	-55 To 150	$^\circ\text{C}$

Thermal Resistance

Parameter	Symbol	Value	Unit
Thermal Resistance, Junction-to-Ambient	R_{thJA}	50	$^\circ\text{C/W}$
Maximum Junction-to-Case	R_{thJC}	8.3	$^\circ\text{C/W}$

Specifications T _J = 25°C, unless otherwise noted						
Parameter	Symbol	Test Conditions	Value			Unit
			Min.	Typ.	Max.	
Static Parameters						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	20	--	--	V
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 20V, V _{GS} = 0V	--	--	1	μA
Gate-Source Leakage	I _{GSS}	V _{GS} = ±12V	--	--	±100	nA
Gate-Source Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	0.5	0.7	1.2	V
Drain-Source On-Resistance	R _{DS(on)}	V _{GS} = 4.5V, I _D = 10A	--	8.5	11	mΩ
		V _{GS} = 2.5V, I _D = 10A	--	11	14	
Forward Transconductance	g _{FS}	V _{GS} = 5V, I _D = 20A	--	56	--	S
Dynamic Parameters						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 10V, f = 1.0MHz	--	1120	--	pF
Output Capacitance	C _{oss}		--	245	--	
Reverse Transfer Capacitance	C _{rss}		--	235	--	
Total Gate Charge	Q _g	V _{DD} = 10V, I _D = 10A, V _{GS} = 4.5V	--	18	--	nC
Gate-Source Charge	Q _{gs}		--	2	--	
Gate-Drain Charge	Q _{gd}		--	6	--	
Turn-on Delay Time	t _{d(on)}	V _{DD} = 10V, I _D = 10A, R _G = 3Ω	--	4.5	--	ns
Turn-on Rise Time	t _r		--	9	--	
Turn-off Delay Time	t _{d(off)}		--	19	--	
Turn-off Fall Time	t _f		--	3	--	
Drain-Source Body Diode Characteristics						
Continuous Body Diode Current	I _S	T _C = 25°C	--	--	26	A
Body Diode Voltage	V _{SD}	T _J = 25°C, I _{SD} = 10A, V _{GS} = 0V	--	--	1.2	V
Reverse Recovery Charge	Q _{rr}	I _F = A, V _{GS} = 0V di/dt=100A/us	--	18	--	nC
Reverse Recovery Time	T _{rr}		--	10	--	ns

Notes

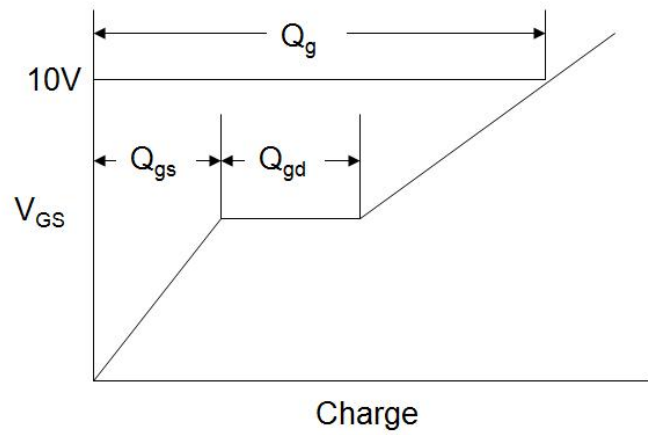
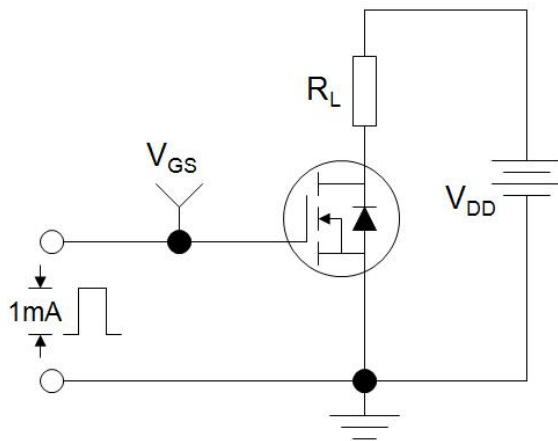
1. Repetitive Rating: Pulse width limited by maximum junction temperature

2. EAS condition : $T_J=25^{\circ}\text{C}$, $V_{DD}=20V$, $V_{GS}=10V$, $L=0.5mH$, $R_g=25\Omega$

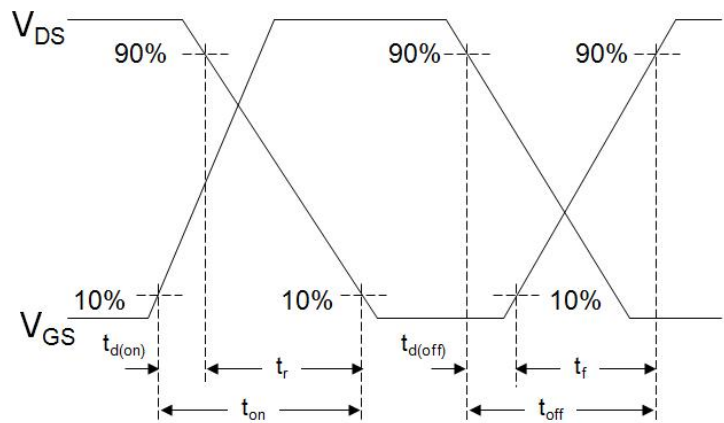
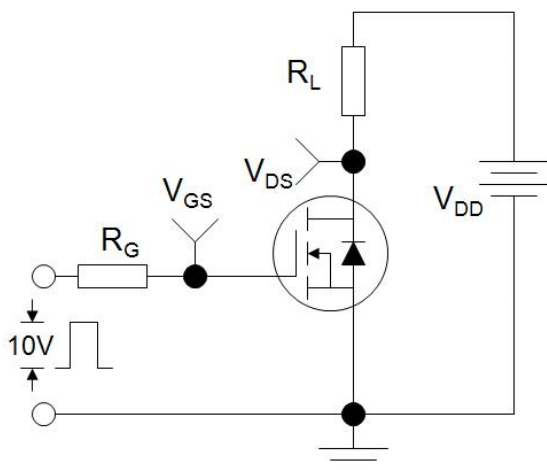
The table shows the minimum avalanche energy, which is 81mJ when the device is tested until failure

3. Identical low side and high side switch with identical R_G

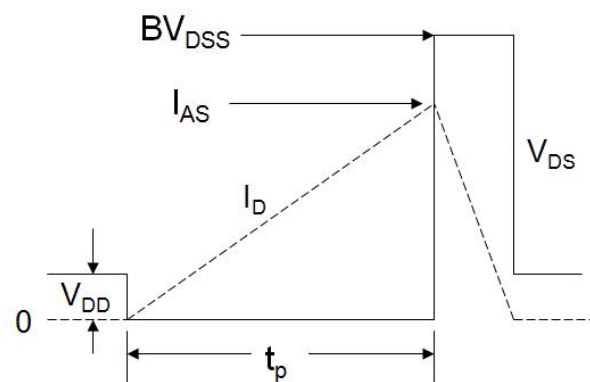
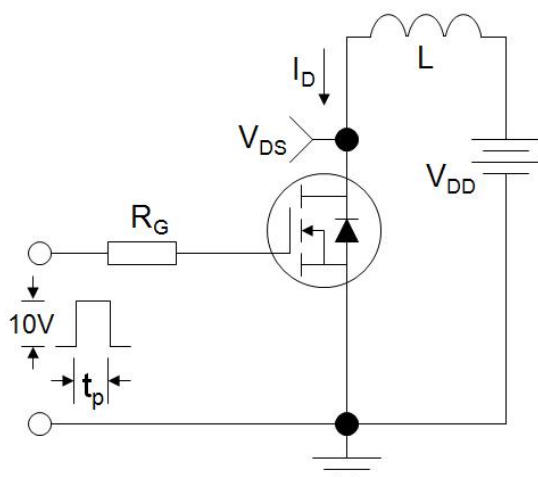
Gate Charge Test Circuit



Switch Time Test Circuit



EAS Test Circuit



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 1. Output Characteristics

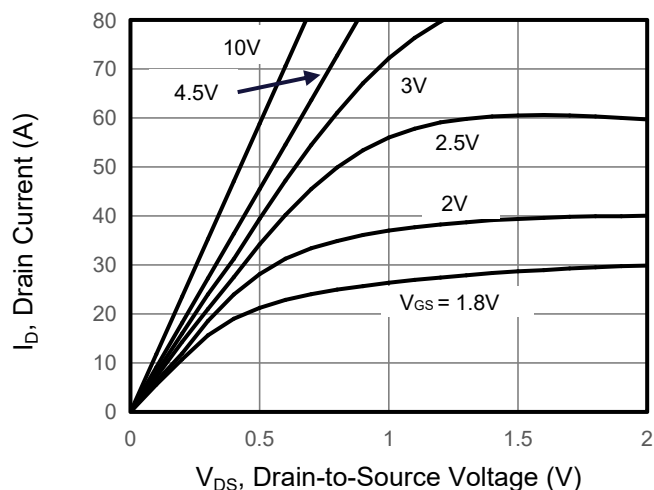


Figure 2. Transfer Characteristics

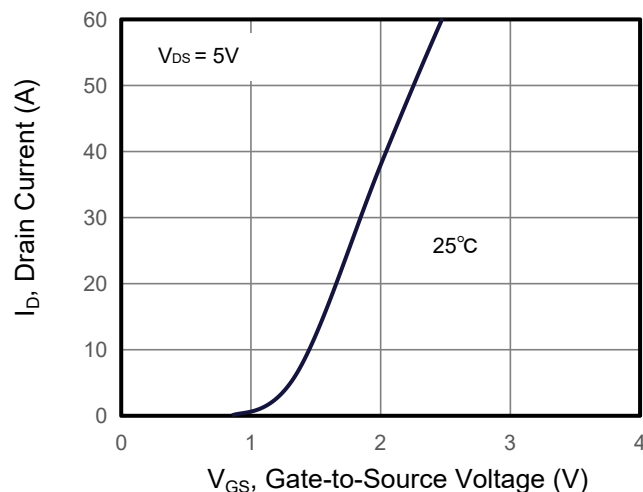


Figure 3. Drain Source On Resistance

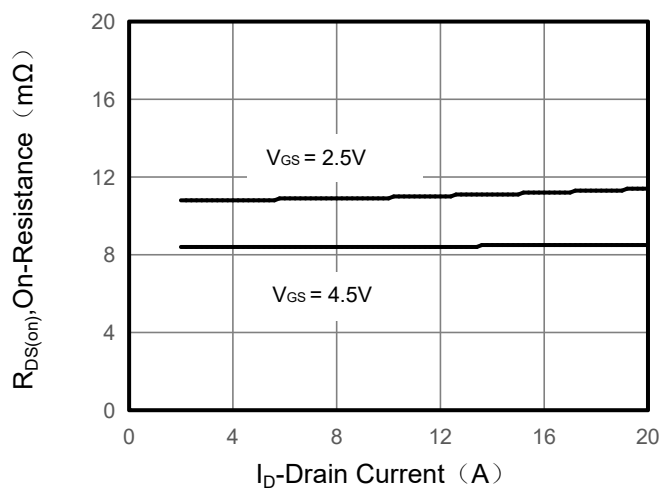


Figure 4. Gate Charge

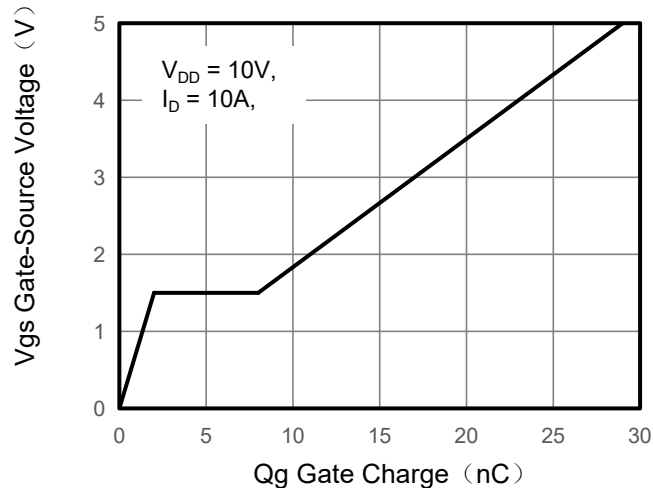


Figure 5. Capacitance

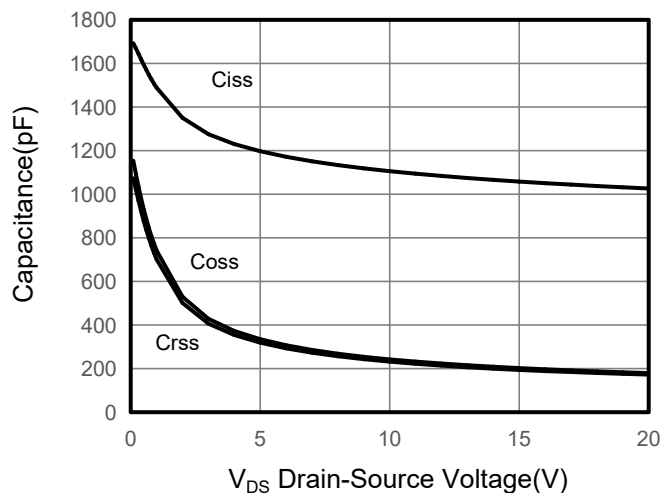
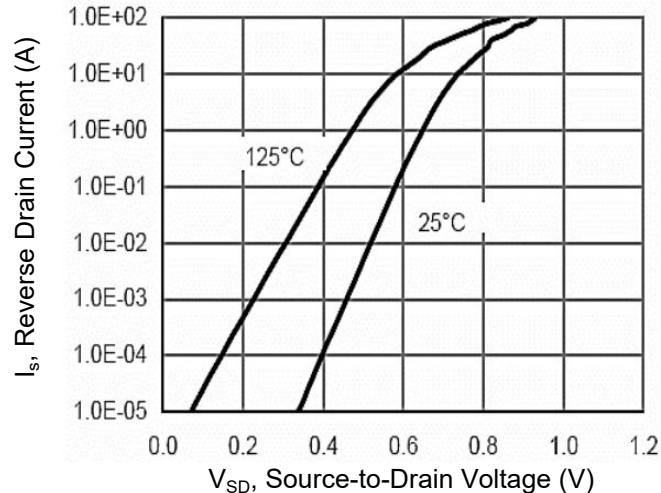


Figure 6. Source-Drain Diode Forward



Typical Characteristics $T_J = 25^\circ\text{C}$, unless otherwise noted

Figure 7. Drain-Source On-Resistance

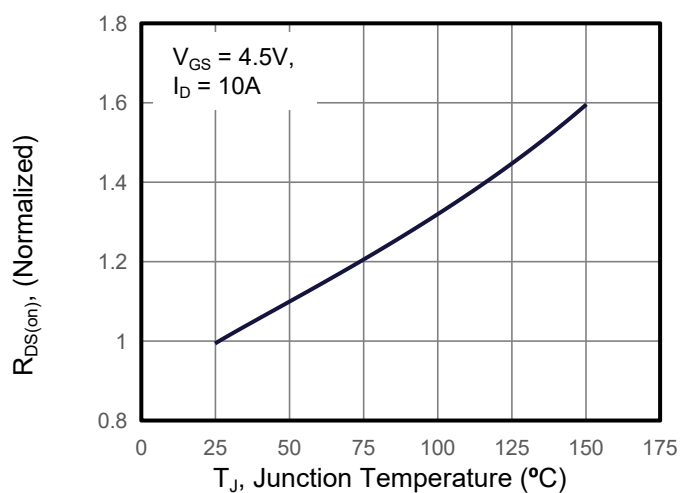


Figure 8. Safe Operation Area

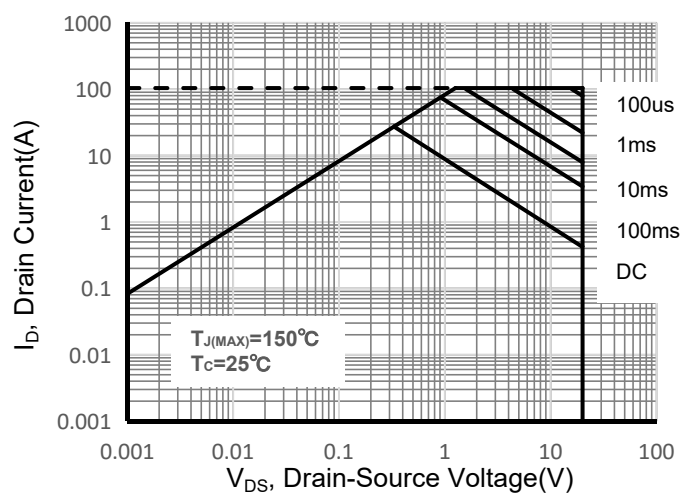


Figure 9. Maximum Continuous Drain Current vs Case Temperature

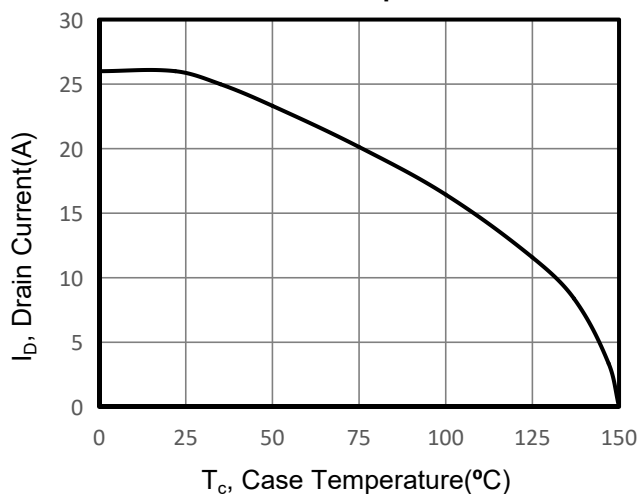
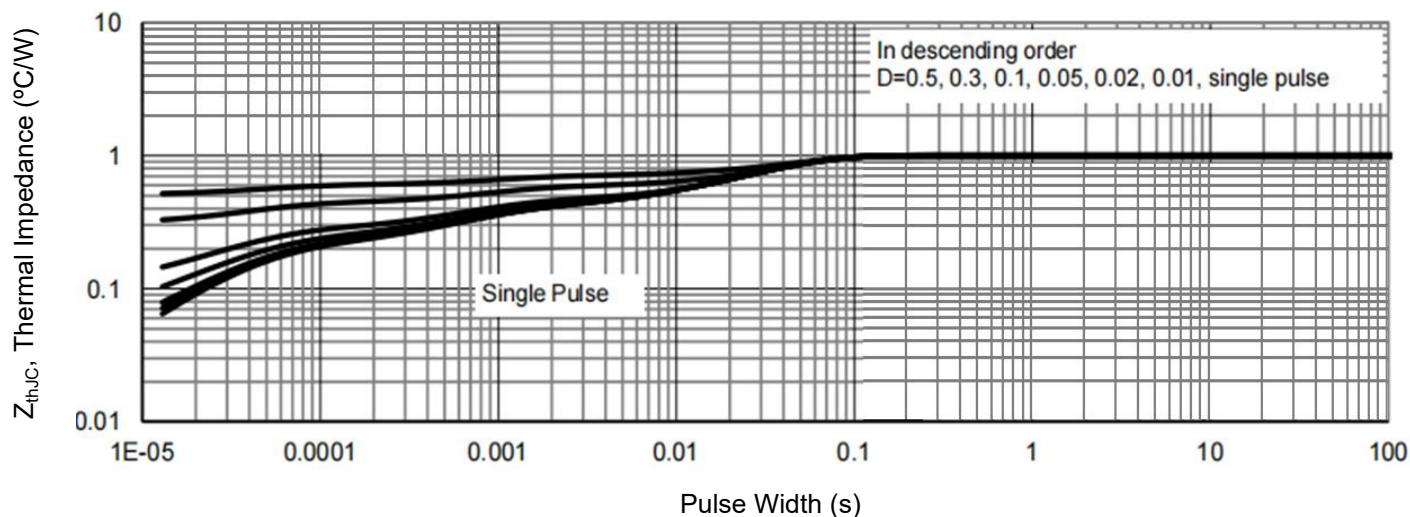
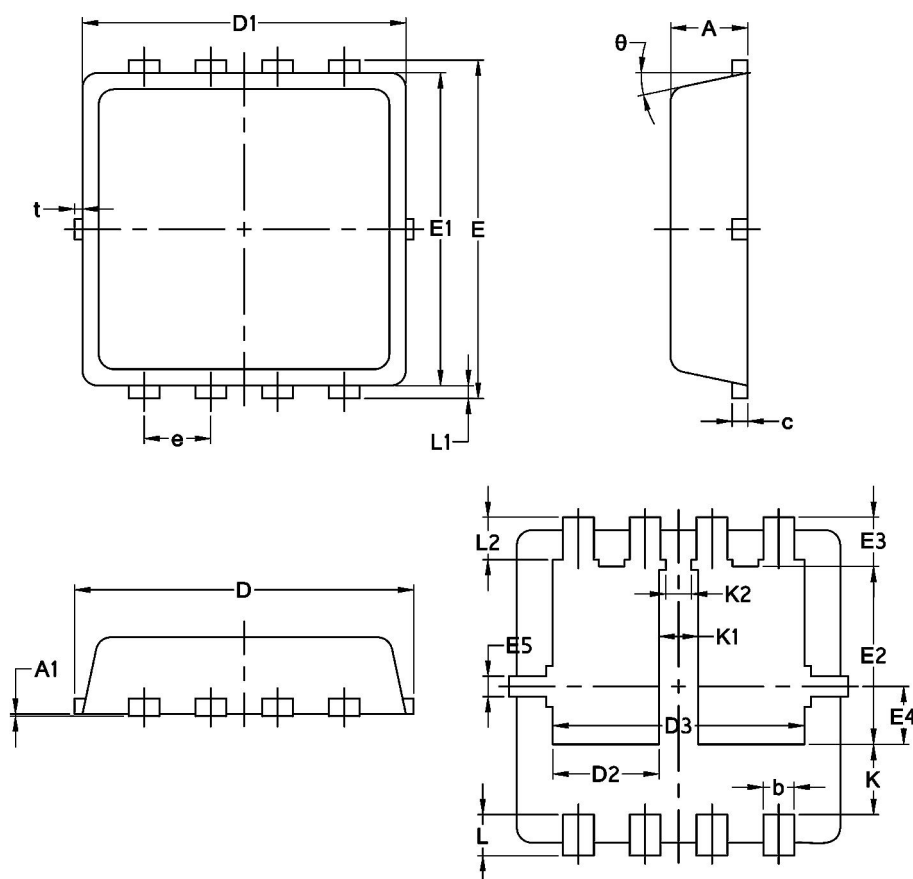


Figure 10. Normalized Maximum Transient Thermal Impedance



DFN3*3-8L Dual Package Information



SYMBOL	COMMON			SYMBOL	COMMON		
	MM				MM		
	MIN	NOM	MAX		MIN	NOM	MAX
A	0.70	0.75	0.85	E4	0.37	0.57	0.77
A1	/	/	0.05	E5	0.10	0.20	0.30
b	0.25	0.30	0.39	e	0.60	0.65	0.70
c	0.14	0.152	0.20	K	0.50	0.69	0.80
D	3.20	3.30	3.45	K1	0.30	0.38	0.53
D1	3.05	3.15	3.25	K2	0.15	0.25	0.35
D2	0.84	1.04	1.24	L	0.30	0.40	0.50
D3	2.30	2.45	2.60	L1	0.06	0.125	0.20
E	3.20	3.30	3.40	L2	0.27	0.42	0.57
E1	2.95	3.05	3.15	t	0	0.075	0.13
E2	1.60	1.74	1.90	θ	10°	12°	14°
E3	0.28	0.48	0.65				

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